Boca Semiconductor Corp. (BSC)

MAXIMUM RATINGS

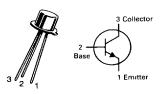
Rating	Symbol	2N930	2N930A	Unit
Collector-Emitter Voltage	VCEO	45	45	Vdc
Collector-Base Voltage	VCBO	45	60	Vdc
Emitter-Base Voltage	VEBO	5.0	6.0	Vdc
Collector Current	lc	30		mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	0.5 3.33		W mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.2 6.9		Watt mW/°C
Operating and Storage Temperature Temperature Range	T _J , T _{stg}	-65 to +175		°C

THERMAL CHARACTERISTICS

HENNIAL CHANACTERISTICS			
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	350	°C/W
Thermal Resistance, Junction to Case	ReJC	146	°C/W

2N930, A

CASE 22-03, STYLE 1 TO-18 (TO-206AA)



AMPLIFIER TRANSISTORS

NPN SILICON

ELECTRICAL CHARACTERISTICS (TA = 25°C unless otherwise noted.)

Characteris	tic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage(1) (IC = 10 mAdc, IB = 0)		V(BR)CEO	45		Vdc
Collector-Base Breakdown Voltage (I _C = 10 μAdc, I _E = 0)	2N930 2N930A	V(BR)CBO	45 60	_	Vdc
Emitter-Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)	2N930 2N930A	V(BR)EBO	5.0 6.0	=	Vdc
Collector Cutoff Current (VCE = 5.0 Vdc, Ig = 0)		ICEO	_	2.0	nAdc
Collector Cutoff Current (V _{CB} = 45 Vdc, I _E = 0)	2N930 2N930A	ICBO		10 2.0	nAdc
Collector Cutoff Current (V _{CB} = 45 Vdc, V _{BE} = 0)	2N930 2N930A	ICES	<u>-</u>	10 2.0	nAdc
$(V_{CE} = 45 \text{ Vdc}, V_{BE} = 0, T_{A} = 170^{\circ}\text{C})$	2N930 2N930A		_	10 2.0	μAdc
Emitter Cutoff Current (VEB = 5.0 Vdc, IC = 0)	2N930 2N930A	lEBO	_	10 2.0	nAdc

ON CHARACTERISTICS

DC Current Gain		hFE	60	_	_
$(I_C = 1.0 \ \mu Adc, V_{CE} = 5.0 \ Vdc)$	2N930A		100	300	
$(I_C = 1.0 \ \mu Adc, V_{CE} = 5.0 \ Vdc)$				•	
$\{I_C = 10 \ \mu Adc, V_{CE} = 5.0 \ Vdc, T_A = -55^{\circ}C\}$	2N930		20	-	
	2N930A	1	30	_	
$(I_C = 500 \mu Adc, V_{CE} = 5.0 Vdc)$	2N930		150	_	,
	2N930A		-	_	
$(I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})(1)$	2N930		_	600	
	2N6304	ì	_	600	1

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2N930, A

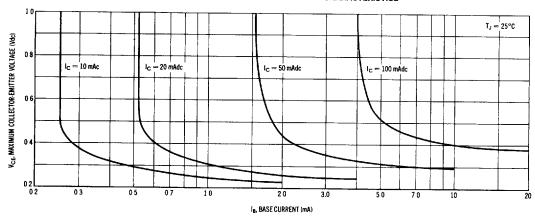
ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted.)

Symbol	Min	Max	Unit	
VCE(sat)	VCE(sat)	VCE(sat)	1.0	Vdc
V _{BE(sat)}	0.6 0.7	1.0	Vdc	
		1 0.3		

Current-Gain — Bandwidth Product (I _C = 500 μ Adc, V _{CE} = 5.0 Vdc, f = 30 MHz)	2N930 2N930A	fT	30 45		MHz
Output Capacitance $(V_{CB} = 5.0 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$	2N930 2N930A	C _{obo}	_	8.0 6.0	pF
Input Impedance (I _E = 1.0 mAdc, V_{CB} = 5.0 Vdc, f = 1.0 kHz)		h _{ib}	25	32	ohms
Voltage Feedback Ratio (I _E = 1.0 mAdc, V _{CB} = 5.0 Vdc, f = 1.0 kHz)		hrb	_	600	X 10 ⁻⁶
Small Signal Current Gain (I _C = 1.0 mAdc, V_{CE} = 5.0 Vdc, f = 1.0 kHz)		h _{fe}	150	600	T -
Output Admittance (IE = 1.0 mAdc, V _{CB} = 5.0 Vdc, f = 1.0 kHz)		h _{ob}		1.0	μmhos
Noise Figure (I _C = 10 μ Adc, V _{CE} = 5.0 Vdc R _S = 10 k ohms, f = 1.0 kHz)		NF		3.0	dB

(1) Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.



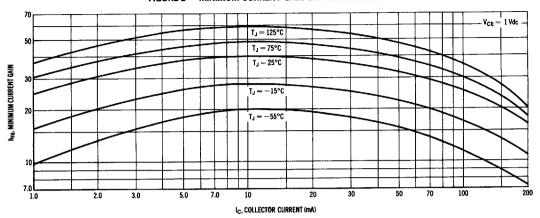


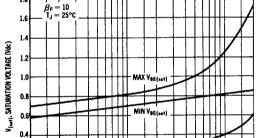
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0.2

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FIGURE 2 — MINIMUM CURRENT GAIN CHARACTERISTICS



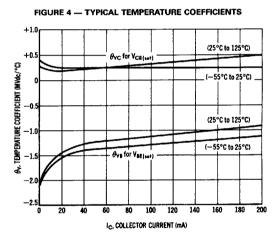


MAX V_{CE(set)}

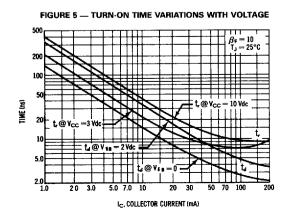
IC, COLLECTOR CURRENT (mA)

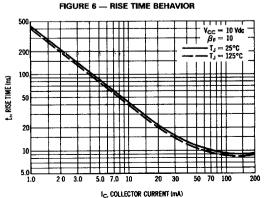
5.0 7.0

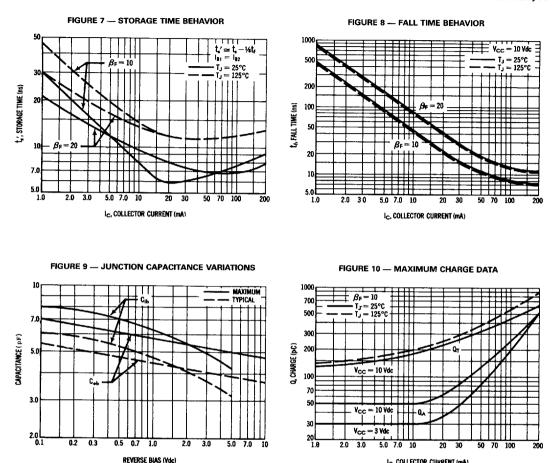
FIGURE 3 — LIMITS OF SATURATION VOLTAGES



TYPICAL SWITCHING CHARACTERISTICS







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IC, COLLECTOR CURRENT (mA)